



N-Channel Silicon MOSFET

# ECH8622R — General-Purpose Switching Device Applications

## Features

- Low ON-resistance.
- Best suited for lithium battery applications.
- 2.5V drive.
- Composite type, facilitating high-density mounting.
- Drain common specifications.

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Drain Current (DC)	I <sub>D</sub>		7	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm) 1unit	1.4	W
Total Dissipation	P <sub>T</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.5		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A	6	10		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V	12.6	18	23	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =4A, V <sub>GS</sub> =4.0V	13.3	19	25	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =4A, V <sub>GS</sub> =3.1V	14.3	22	29	mΩ
	R <sub>DS(on)4</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =2.5V	15	25	34	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		1220		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		180		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		140		pF

Marking : WG

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# ECH8622R

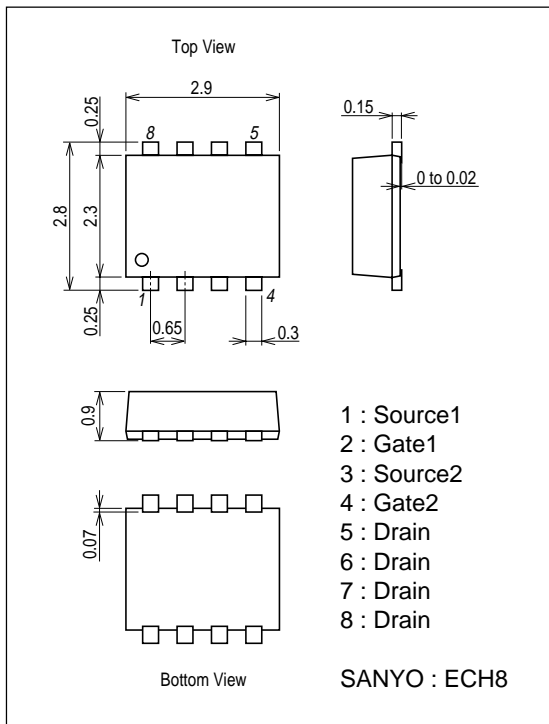
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		585		ns
Rise Time	$t_r$	See specified Test Circuit.		1680		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		4960		ns
Fall Time	$t_f$	See specified Test Circuit.		2660		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		14		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		2		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		4.3		nC
Diode Forward Voltage	$V_{SD}$	$I_S=7A, V_{GS}=0V$		0.84	1.2	V

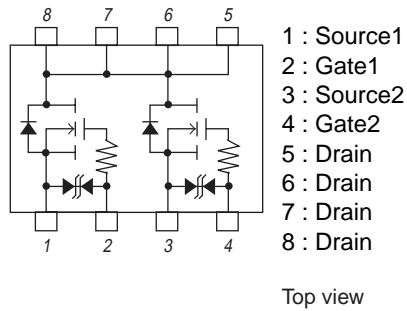
## Package Dimensions

unit : mm

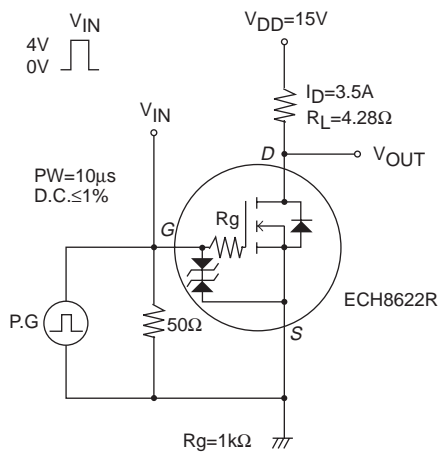
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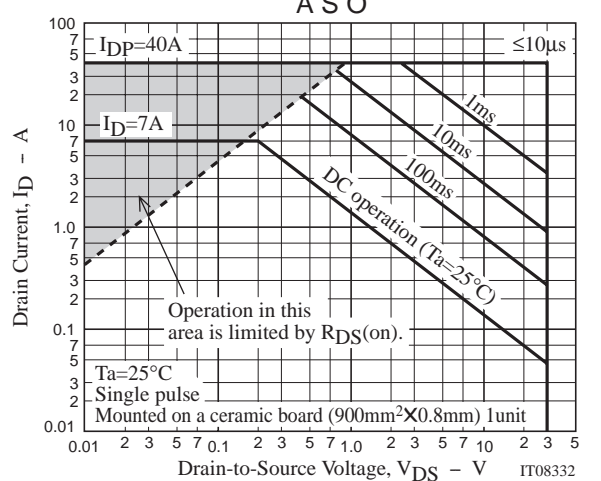
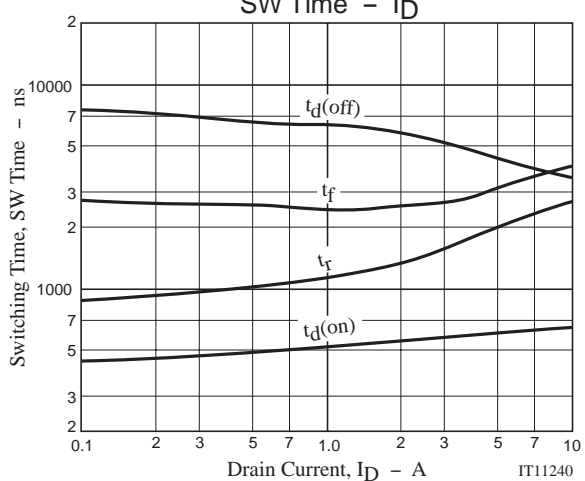
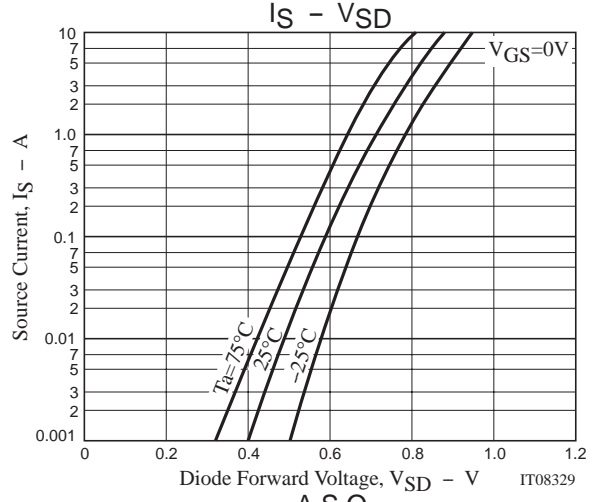
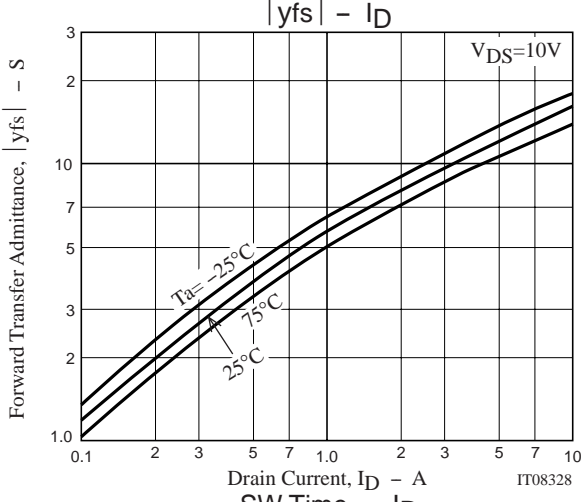
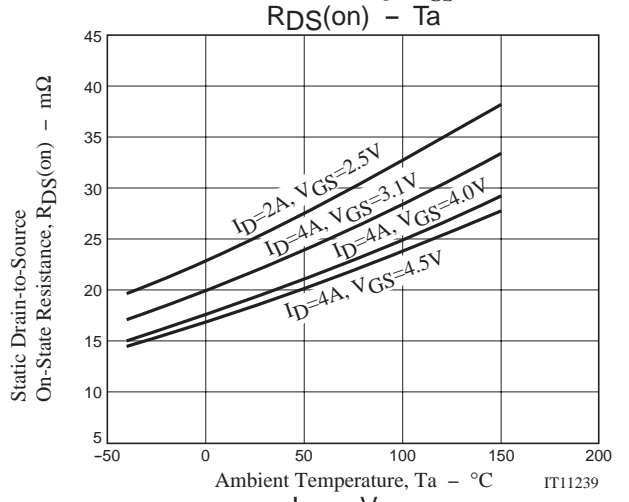
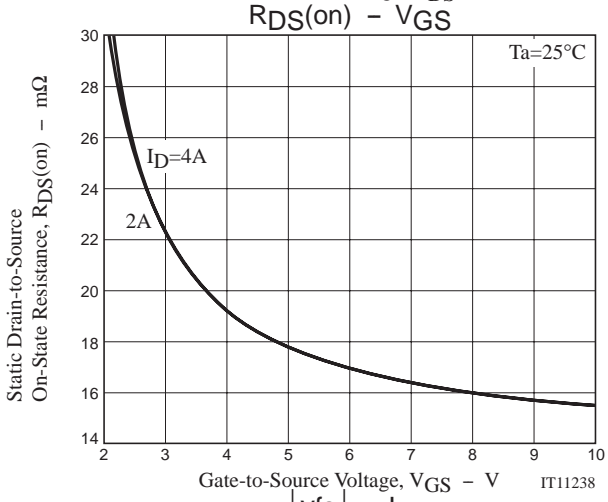
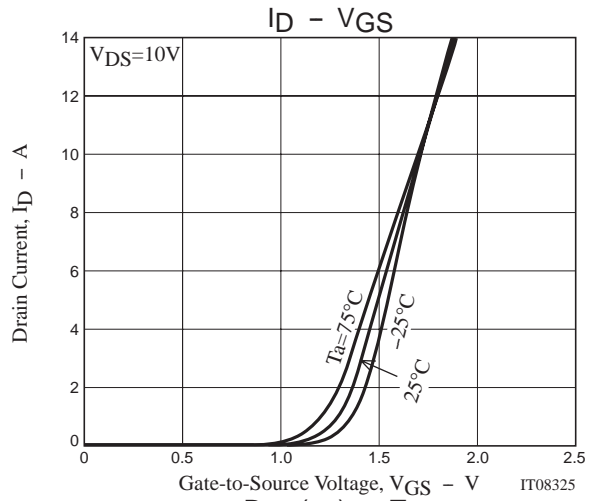
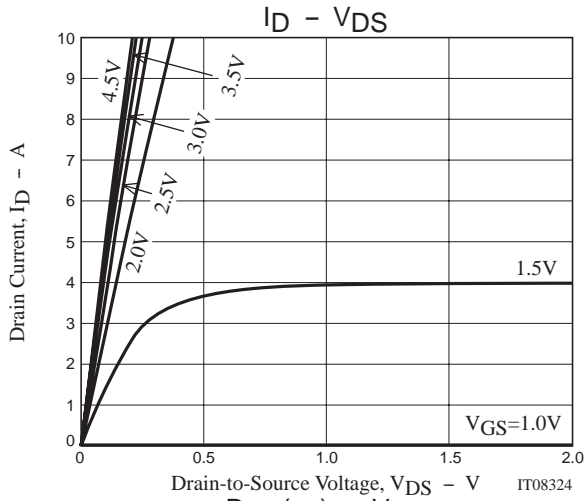
## Electrical Connection

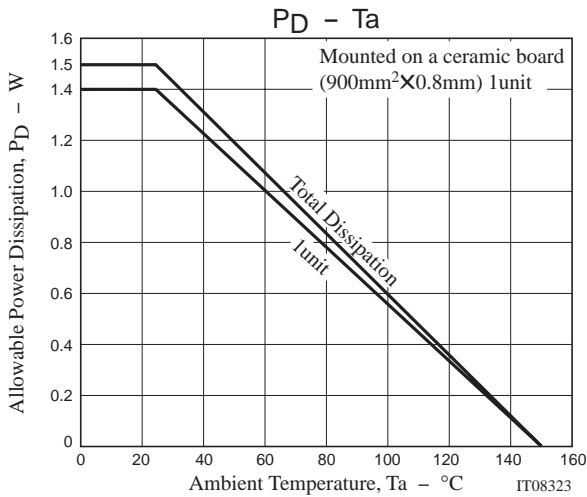


## Switching Time Test Circuit



# ECH8622R





Note on usage : Since the ECH8622R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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